

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1.-59. (Canceled)

60. (Currently Amended) A semiconductor device comprising:

a substrate having a front surface and a rear surface;

a first insulating film comprising silicon oxide provided over said front surface of said substrate;

a second insulating film comprising aluminum nitride and oxygen provided over said first insulating film;

a third insulating film comprising oxide provided over said second insulating film;

a transistor provided over said third insulating film, said transistor having at least a channel formation region, a source region, a drain region, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween;

an interlayer insulating film comprising a leveled upper surface over said transistor;  
and

a pixel electrode over said interlayer insulating film[.],

wherein crystallinity of said source region or the drain region is higher than crystallinity of said channel region.

61. (Currently Amended) A semiconductor device comprising:

a substrate comprising a front surface and a rear surface;

a first insulating film comprising silicon oxide provided over said front surface of said substrate;

a second insulating film comprising aluminum nitride and oxygen provided over said first insulating film;

a third insulating film comprising oxide provided over said second insulating film;

a transistor provided over said third insulating film, said transistor having at least a channel formation region, a source region, a drain region, a gate insulating film adjacent to

said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween;

an insulating film over said transistor; and

a pixel electrode over said insulating film[.],

wherein crystallinity of said source region or the drain region is higher than crystallinity of said channel region.

62. (Previously Presented) The device of claim 60 wherein said substrate is a glass substrate.

63. (Previously Presented) The device of claim 61 wherein said substrate is a glass substrate.

64.-67. (Canceled)

68. (Currently Amended) A semiconductor device comprising:

a substrate;

a first insulating film comprising silicon oxide;

a second insulating film comprising aluminum nitride formed on said first insulating film;

a third insulating film comprising silicon oxide formed on said second insulating film;

and

~~a semiconductor film formed on said third insulating film;~~

~~a gate insulating film formed on said semiconductor film; and~~

~~a gate electrode formed on said gate insulating film.~~

a transistor provided over said third insulating film, said transistor having at least a channel formation region, a source region, a drain region, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween,

wherein crystallinity of said source region or the drain region is higher than crystallinity of said channel region.

69. (Previously Presented) The semiconductor device according to claim 68, wherein said semiconductor device is an active matrix display device.

70. (Previously Presented) The semiconductor device according to claim 68, wherein said semiconductor device comprises a pixel portion and a driver portion over said substrate.

71.-76. (Canceled)

77. (Currently Amended) A semiconductor device comprising:  
a substrate;  
a first insulating film comprising silicon oxide;  
a second insulating film comprising aluminum nitride formed on said first insulating film;  
a third insulating film comprising oxide formed on said second insulating film; and  
~~a semiconductor film formed on said third insulating film;~~  
~~a gate insulating film formed on said semiconductor film; and~~  
~~a gate electrode formed on said gate insulating film.~~  
a transistor provided over said third insulating film, said transistor having at least a channel formation region, a source region, a drain region, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween,  
wherein crystallinity of said source region or the drain region is higher than crystallinity of said channel region.

78. (Previously Presented) The semiconductor device according to claim 77, wherein said semiconductor device is an active matrix display device.

79. (Previously Presented) The semiconductor device according to claim 77, wherein said semiconductor device comprises a pixel portion and a driver portion over said substrate.

80.-87. (Canceled)

88. (New) The semiconductor device according to claim 68,  
wherein said transistor comprises:

a semiconductor film formed on said third insulating film, said semiconductor film comprising at least said channel formation region, said source region, and said drain region;

a gate insulating film formed on said semiconductor film; and

a gate electrode formed on said gate insulating film.

89. (New) The semiconductor device according to claim 77,  
wherein said transistor comprises:

a semiconductor film formed on said third insulating film, said semiconductor film comprising at least said channel formation region, said source region, and said drain region;

a gate insulating film formed on said semiconductor film; and

a gate electrode formed on said gate insulating film.